

Chang-Ju Lee

List of Publications by Year in descending order

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26
papers

187
citations

1307594

7
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1058476

14
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26
all docs

26
docs citations

26
times ranked

320
citing authors

#	ARTICLE	IF	CITATIONS
1	Optimized poly(methyl methacrylate)-mediated graphene-transfer process for fabrication of high-quality graphene layer. <i>Nanotechnology</i> , 2018, 29, 415303.	2.6	41
2	Selectively Enhanced UV-A Photoresponsivity of a GaN MSM UV Photodetector with a Step-Graded Al _x Ga _{1-x} N Buffer Layer. <i>Sensors</i> , 2017, 17, 1684.	3.8	22
3	GaN metal-“semiconductor”-metal UV sensor with multi-layer graphene as Schottky electrodes. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 06FF08.	1.5	20
4	Dual-wavelength sensitive AlGaIn/GaN metal-insulator-semiconductor-insulator-metal ultraviolet sensor with balanced ultraviolet/visible rejection ratios. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	17
5	GaN-Based Ultraviolet Passive Pixel Sensor on Silicon (111) Substrate. <i>Sensors</i> , 2019, 19, 1051.	3.8	14
6	Hybrid UV Active Pixel Sensor Implemented Using GaN MSM UV Sensor and Si-Based Circuit. <i>IEEE Sensors Journal</i> , 2015, 15, 5071-5074.	4.7	11
7	Multifunctional graphene sensor for detection of environment signals using a decoupling technique. <i>Solid-State Electronics</i> , 2019, 151, 40-46.	1.4	8
8	Analytic model of spalling technique for thickness-controlled separation of single-crystalline semiconductor layers. <i>Solid-State Electronics</i> , 2020, 163, 107660.	1.4	8
9	Effect of copper surface morphology on grain size uniformity of graphene grown by chemical vapor deposition. <i>Current Applied Physics</i> , 2019, 19, 1414-1420.	2.4	7
10	Layer-resolved release of epitaxial layers in III-V heterostructure via a buffer-free mechanical separation technique. <i>Science Advances</i> , 2022, 8, eabl6406.	10.3	7
11	Graphene/Al ₂ O ₃ /AlGaIn/GaN Schottky MISIM Diode for Sensing Double UV Bands. <i>IEEE Sensors Journal</i> , 2016, 16, 6903-6907.	4.7	6
12	GaN schottky barrier MOSFET using transparent source/drain electrodes for UV-optoelectronic integration. <i>Solid-State Electronics</i> , 2012, 73, 78-80.	1.4	5
13	Investigation of electrical characteristics of flexible CMOS devices fabricated with thickness-controlled spalling process. <i>Solid-State Electronics</i> , 2020, 173, 107901.	1.4	5
14	Extraction of intrinsic field-effect mobility of graphene considering effects of gate-bias-induced contact modulation. <i>Journal of Applied Physics</i> , 2020, 127, .	2.5	5
15	Performance of GaN Metal-“Oxide”-Semiconductor Field-Effect Transistor with Regrown n ⁺ -Source/Drain on a Selectively Etched GaN. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 061001.	1.5	4
16	Effect of Graphene Doping Level near the Metal Contact Region on Electrical and Photoresponse Characteristics of Graphene Photodetector. <i>Sensors</i> , 2020, 20, 4661.	3.8	3
17	Simultaneous Extraction of the Grain Size, Single-Crystalline Grain Sheet Resistance, and Grain Boundary Resistivity of Polycrystalline Monolayer Graphene. <i>Nanomaterials</i> , 2022, 12, 206.	4.1	2
18	Enhanced UV-visible rejection ratio in an MSM UV photodetector fabricated on N-face GaN by thermal annealing effects. , 2012, , .		1

#	ARTICLE	IF	CITATIONS
19	Evaluation of the average grain size of polycrystalline graphene using an electrical characterization method. Solid-State Electronics, 2021, 186, 108172.	1.4	1
20	Body bias effect of GaN schottky barrier MOSFET with ITO source/drain. , 2010, , .		0
21	GaN schottky barrier MOSFET using indium-tin-oxide as source, drain and gate material. , 2010, , .		0
22	Vertical GaN schottky barrier diode on an N-face GaN layer formed by ELOG and laser-lift-off technique for high-power application. , 2011, , .		0
23	UV-A selective photo-responsivity in a GaN MSM photodetector using ITO schottky electrodes. , 2011, , .		0
24	Dual-band responsivity of AlGaIn/GaN MSM UV photodiode. , 2012, , .		0
25	High UV-visible rejection ratio of dual-wavelength detecting MISIM UV sensor with a thin Al ₂ O ₃ layer. , 2013, , .		0
26	Double-wavelength sensitive AlGaIn/GaN MISIM UV sensor using multi-layer graphene as Schottky electrodes. , 2015, , .		0